

isc Silicon NPN Power Transistor
2SC4110
DESCRIPTION

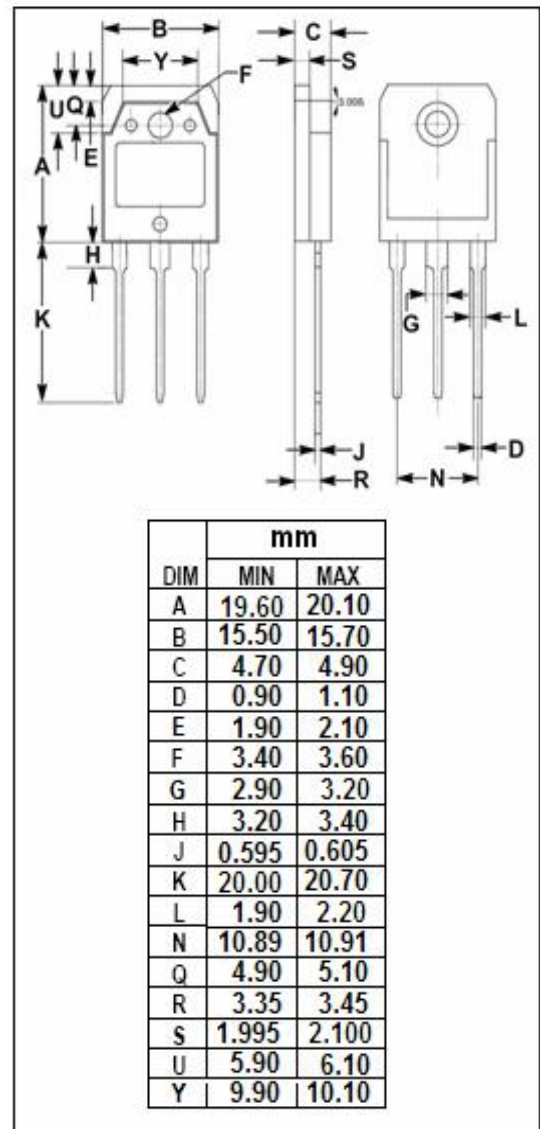
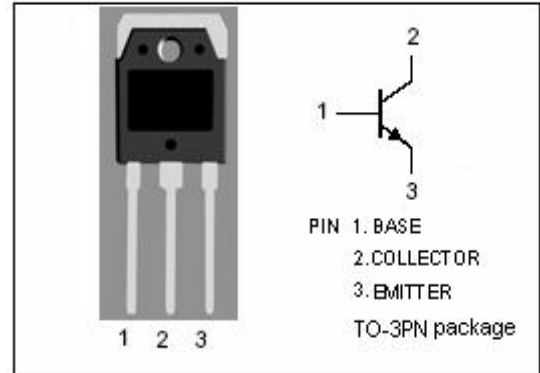
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 400V(\text{Min})$
- High Switching Speed
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for switching regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base voltage	7	V
I_C	Collector Current-Continuous	25	A
I_{CM}	Collector Current-Peak $PW \leq 300\mu\text{s}$, duty cycle $\leq 10\%$	40	A
I_B	Base Current-Continuous	8	A
P_C	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	160	W
	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	2.5	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

 T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA; I _E = 0	500			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; R _{BE} = ∞	400			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 16A; I _B = 3.2A			0.8	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 16A; I _B = 3.2A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 400V ; I _E = 0			10	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μA
h _{FE-1}	DC Current Gain	I _C = 3.2A ; V _{CE} = 5V	15		50	
h _{FE-2}	DC Current Gain	I _C = 16A ; V _{CE} = 5V	10			
h _{FE-3}	DC Current Gain	I _C = 10mA ; V _{CE} = 5V	10			
f _T	Current-Gain—Bandwidth Product	I _C = 3.2A ; V _{CE} = 10V		20		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1.0MHz		300		pF

Switching Times

t _{on}	Turn-on Time	I _C = 20A, I _{B1} = 4A; I _{B2} = -8A R _L = 10 Ω; V _{CC} = 200V			0.5	μs
t _{stg}	Storage Time				2.5	μs
t _f	Fall Time				0.3	μs

◆ h_{FE-1} Classifications

L	M	N
15-30	20-40	30-50

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